Amend th claims to read as follows.

SUB B8 7

1. (amended) A method for forming a gate dielectric for an integrated circuit device, the method comprising:

forming an initial oxynitride layer upon a substrate material, said initial oxynitride layer having an initial thickness; and

subjecting said initial oxynitride layer to a plasma nitridation, said plasma nitridation resulting in final oxynitride layer, said final oxynitride layer having a final thickness,

A1 wherein said final oxynitride layer has an equivalent oxide thickness of less than 15 angstroms and a nitrogen concentration of at least $2.0 \times 10^{15}$ atoms/$cm^2$.

2. (amended) The method of claim 1, wherein said final thickness exceeds said initial thickness by less than 5 angstroms.

3. (amended) The method of claim 1, wherein said final thickness is less than 20 angstroms.

## REMARKS

This Amendment has been revised in light of the Office Action mailed February 28, 2002. Claims 1-3 and 6-8 are presented for examination. Claims 4, 5 and 9-13 have been canceled without prejudice. Claim 1 has been amended to incorporate the limitations of Claims 4 and 5, and Claims 2 and 3 also have been amended. Pursuant to 37 C.F.R. § 1.121(c)(1), a marked up version of the amended claims is presented in an appendix to this Amendment.

Election/Restrictions

Election of one of the following two groups of claims is required: (I) Claims 1-8 drawn to a method; and (II) Claims 9-13 drawn to a device. Applicants hereby affirm the



Received from < 914 892 6363 > at 5/28/02 3:16:54 PM [Eastern Daylight Time]